Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L4	31	(((bi dual tween double) near3 level) near5 (cell memory)) with (recess trench groove hole via aperture)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/03/02 07:38
L5	815	(((bi dual tween double) near3 level) near5 (cell memory))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/03/02 08:02
L6	16094	(memory near3 (cell device)) with ((control floating) near3 gate)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/03/02 07:39
L7	4593	L6 and (polysilicon near3 gate)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/03/02 08:00
L8	16094	(memory near3 (cell device)) with ((control floating) near3 gate)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/03/02 08:00
L9	4593	8 and (polysilicon near3 gate)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/03/02 08:00
L10	99	9 and (((bi dual tween double) near3 level) with (cell memory))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/03/02 08:02
S22	16076	(memory near3 (cell device)) with ((control floating) near3 gate)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/03/02 08:00
S23	16113	(memory near3 (cell device)) with ((control floating) near3 gate)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/03/01 16:25
S24	4594	S23 and (polysilicon near3 gate)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/03/02 07:39

S26	666	((bi dual) near3 level) with memory	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/03/01 16:32
S27	26	S24 and ((bi dual) near3 level) with memory	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/03/02 07:31